

UTC UNISONIC TECHNOLOGIES CO., LTD

UT3416B **Preliminary** Power MOSFET

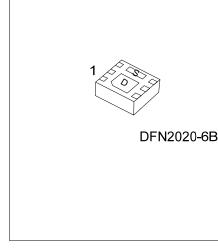
6.5A, 20V N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

DESCRIPTION

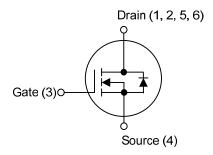
The UTC UT3416B is advanced N-channel enhancement MOSFET which can provide the designer with the best combination of excellent R_{DS (ON)}, low gate charge and low gate voltages as low as 1.8V.When it is used as a load switch or in PWM application, the UTC UT3416B can be considered as an ideal.



* $R_{DS(ON)} \le 20 \text{ m}\Omega$ @ V_{GS} =4.5V, I_D =6.5A $R_{DS(ON)} \le 26 \text{ m}\Omega$ @ $V_{GS} = 2.5 \text{V}$, $I_D = 5.5 \text{A}$ $R_{DS(ON)} \le 36 \text{ m}\Omega @ V_{GS} = 1.8V, I_D = 5.0A$



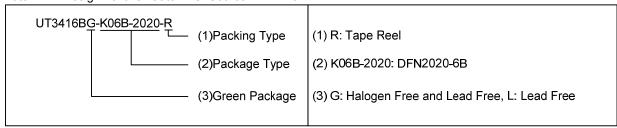
SYMBOL



ORDERING INFORMATION

Ordering Number		Doolsone	Pin Assignment					Daaldaa		
Lead Free	Halogen Free	Package	1	2	3	4	5	6	Packing	
UT3416BL-K06B-2020-R	UT3416BG-K06B-2020-R	DFN2020-6B	D	D	G	S	D	D	Tape Reel	

Note: Pin Assignment: G: Gate S: Source D: Drain



MARKING



www.unisonic.com.tw 1 of 3

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{ extsf{DSS}}$	20	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current	I _D	6.5	Α
Pulsed Drain Current (Note 2)	I _{DM}	30	Α
Power Dissipation (Note 3)	P_{D}	1.9	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T _{STG}	-55 ~ + 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. Surface mounted on 1in² copper pad of FR4 board.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	65	°C/W

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_{D} =250 μ A	20			V
Drain-Source Leakage Current	I _{DSS}	V _{GS} =0V, V _{DS} =16V			1	μΑ
Gate-Source Leakage Current	I _{GSS}	V_{GS} =±8V, V_{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.4	0.6	1.0	V
		V _{GS} =4.5V, I _D =6.5A		14	20	mΩ
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =5.5A		20	26	mΩ
		V _{GS} =1.8V, I _D =5.0A		28	36	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			680		pF
Output Capacitance	Coss	V_{GS} =0V, V_{DS} =10V, f =1MHz		240		pF
Reverse Transfer Capacitance	C_{RSS}			220		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G			20		nC
Gate Source Charge	Q_GS	V_{DS} =16V, V_{GS} =4.5V, I_{D} =6.5A		3		nC
Gate Drain Charge	Q_GD			7		nC
Turn-ON Delay Time	t _{D(ON)}			20		ns
Turn-ON Rise Time	t_R V_{DS} =10V, V_{GS} =4.5V, I_D =6.5A,			27		ns
Turn-OFF Delay Time	t _{D(OFF)}	$R_G=3.3\Omega$		40		ns
Turn-OFF Fall-Time	t _F			28		ns
SOURCE- DRAIN DIODE RATINGS	AND CHARA	CTERISTICS				
Diode Forward Voltage	V_{SD}	I _S =1.0A, V _{GS} =0V		0.76	1	V

Notes: 1. Pulse Test: Pulse width \leq 300 μ s, Duty cycle \leq 2%.

2. Essentially independent of operating temperature.

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.